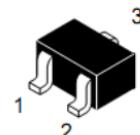


WNM3018

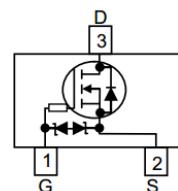
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

Small Signal N-Channel, 50V, 0.2A, MOSFET

V_{DS} (V)	Typical R_{Ds(on)} (Ω)
50	1.2@ V _{GS} =10V
	1.4@ V _{GS} =4.5V
	1.9@ V _{GS} =2.5V
	5.4@ V _{GS} =1.8V
ESD Rating: 2000V HBM	



SOT-323

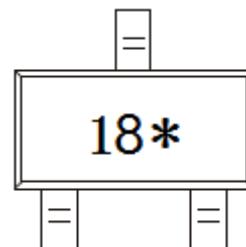


Pin configuration (Top view)

The WNM3018 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{Ds(ON)} with low gate charge. This device is suitable for use in small signal switch. Standard Product WNM3018 is Pb-free and Halogen-free.

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- HBM ESD protection >2 kV
- Small package SOT-323



18 = Device Code
* = Month (A~Z)

Marking

Applications

- Driver: Relay, Solenoid, Lamps,Hammers etc.
- Power supply converters circuit
- Load/Power Switching for potable device

Order information

Device	Package	Shipping
WNM3018-3/TR	SOT-323	3000/Reel&Tape

Absolute Maximum ratings

Parameter	Symbol	10 S	Steady State	Unit
Drain-Source Voltage	V _{DS}	50		V
Gate-Source Voltage	V _{GS}	±20		
Continuous Drain Current ^{a d}	T _A =25°C	I _D	0.25	A
	T _A =70°C		0.20	
Maximum Power Dissipation ^{a d}	T _A =25°C	P _D	0.37	W
	T _A =70°C		0.24	
Continuous Drain Current ^{b d}	T _A =25°C	I _D	0.22	A
	T _A =70°C		0.17	
Maximum Power Dissipation ^{b d}	T _A =25°C	P _D	0.28	W
	T _A =70°C		0.18	
Pulsed Drain Current ^c	I _{DM}		1.0	A
Operating Junction Temperature	T _J		-55 to 150	°C
Lead Temperature	T _L		260	°C
Storage Temperature Range	T _{stg}		-55 to 150	°C

Thermal resistance ratings

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	t ≤ 10 s	R _{θJA}	285	335
	Steady State		340	
Junction-to-Ambient Thermal Resistance ^b	t ≤ 10 s	R _{θJA}	385	450
	Steady State		455	
Junction-to-Case Thermal Resistance	R _{θJC}	260	300	

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

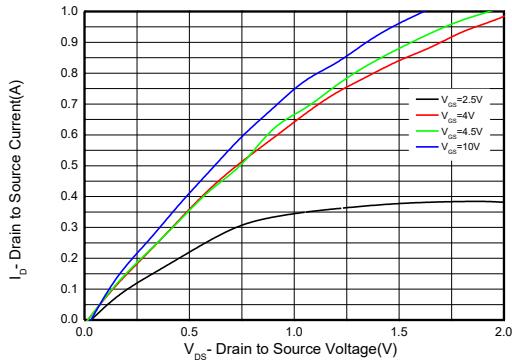
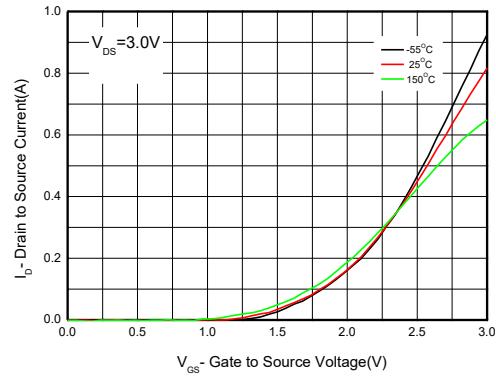
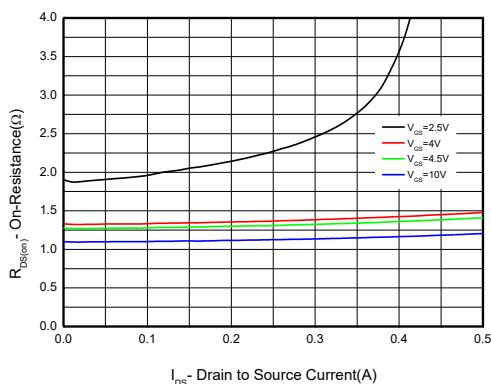
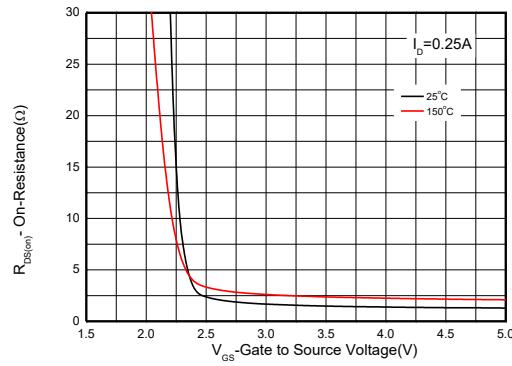
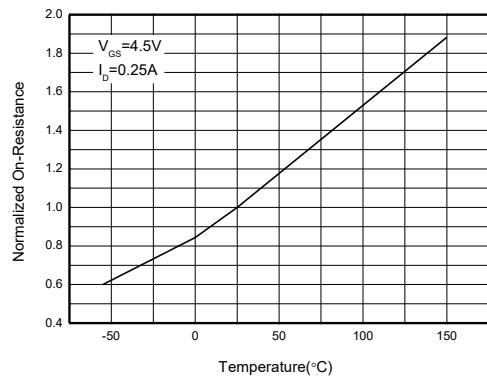
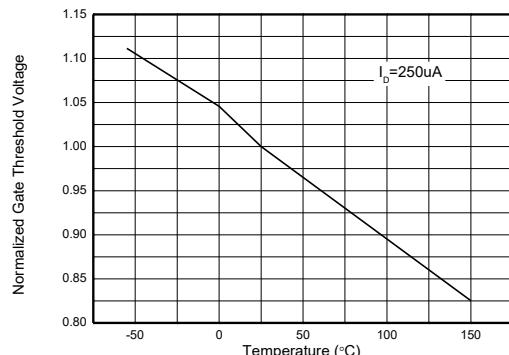
b Surface mounted on FR-4 board using minimum pad size, 1oz copper

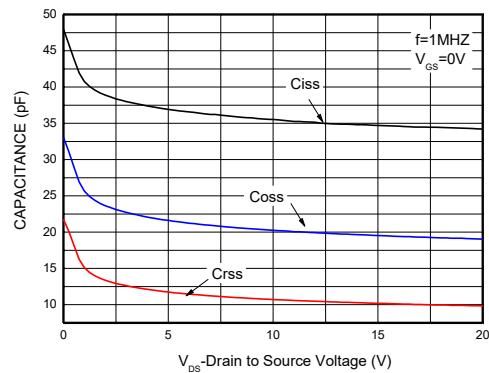
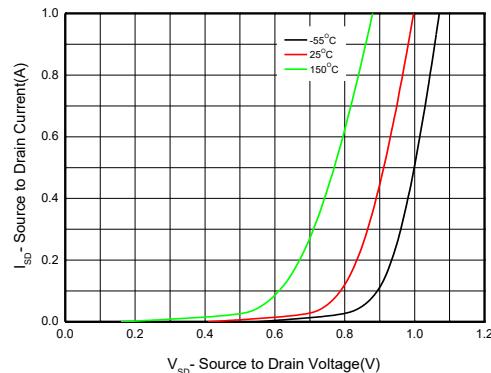
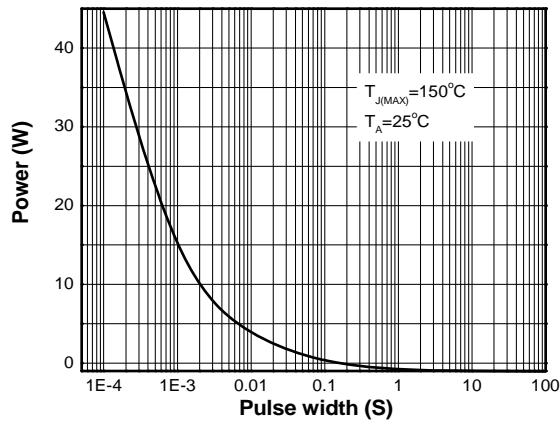
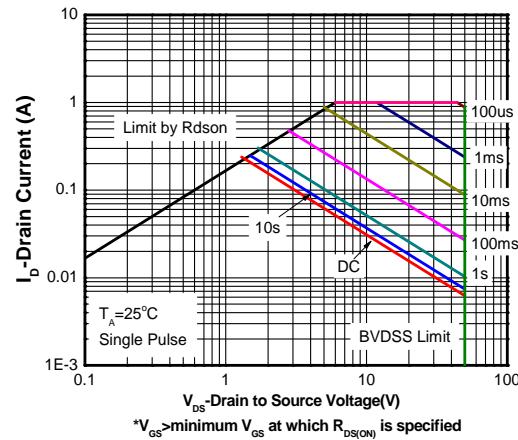
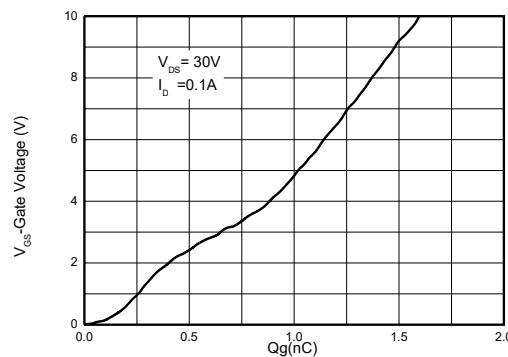
c Pulse width<380μs, Duty Cycle<2%

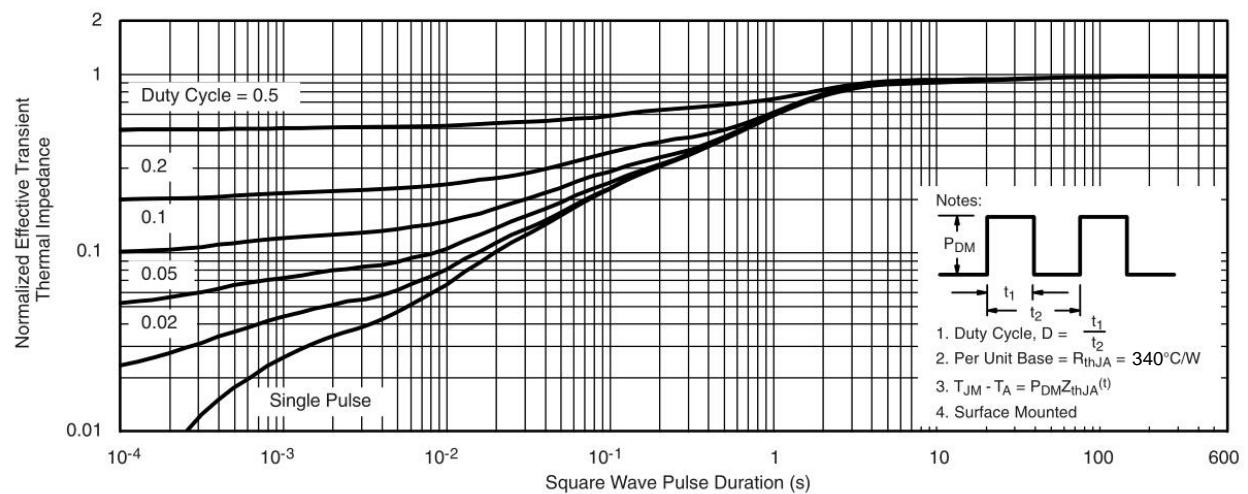
d Maximum junction temperature T_J=150°C.

Electronics Characteristics (Ta=25°C, unless otherwise noted)

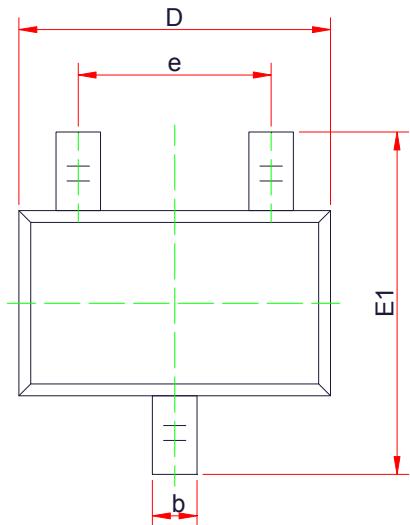
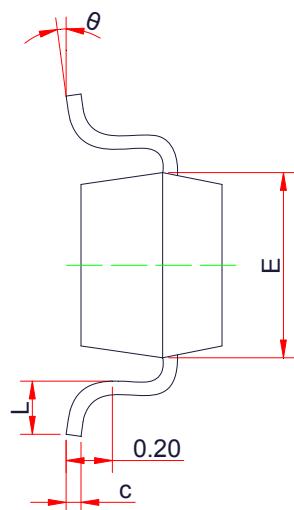
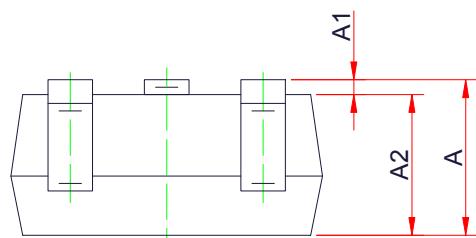
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	50			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20V			±5	uA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	0.7	1.0	1.5	V
Drain-to-source On-resistance ^{b, c}	R _{DS(on)}	V _{GS} = 10V, I _D = 0.45A		1.2	3	Ω
		V _{GS} = 4.5V, I _D = 0.25A		1.3	4	
		V _{GS} = 2.5V, I _D = 0.01A		1.9	6	
		V _{GS} = 1.8V, I _D = 0.01A		5.4	15	
Forward Trans conductance	g _{fs}	V _{DS} = 15V, I _D = 0.1A		0.5		S
CAPACITANCES, CHARGES						
Input Capacitance	C _{ISS}	V _{GS} = 0 V,		36		pF
Output Capacitance	C _{OSS}	F = 1.0 MHz,		22		
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 5 V		12		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DD} = 30 V, I _D = 0.1 A		1.6		nC
Threshold Gate Charge	Q _{G(TH)}			0.25		
Gate-to-Source Charge	Q _{GS}			0.4		
Gate-to-Drain Charge	Q _{GD}			0.45		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V _{GS} = 5 V, V _{DD} = 5 V, R _L =500 Ω, R _G =10 Ω, I _D = 10m A		8.6		ns
Rise Time	tr			4		
Turn-Off Delay Time	td(OFF)			23.8		
Fall Time	tf			14.2		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 0.25A		0.8	1.5	V

Typical Characteristics (Ta=25°C, unless otherwise noted)

Output characteristics

Transfer characteristics

On-Resistance vs. Drain current

On-Resistance vs. Gate-to-Source voltage

On-Resistance vs. Junction temperature

Threshold voltage vs. Temperature

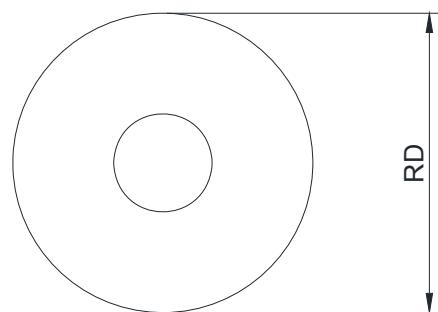
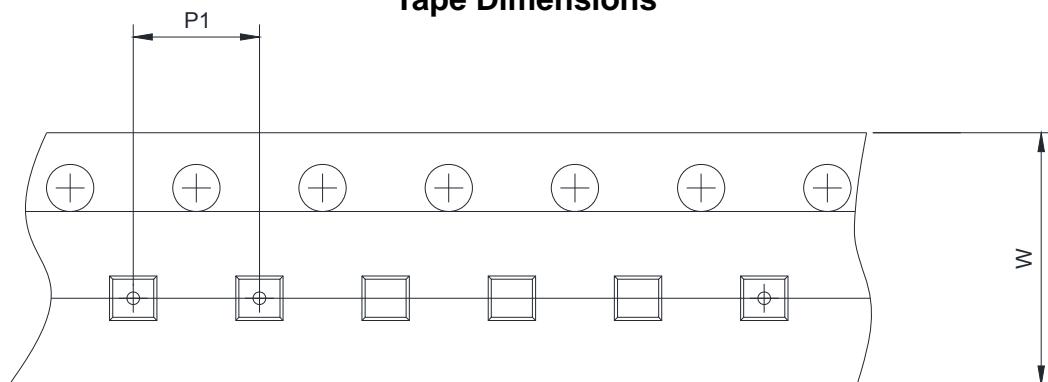
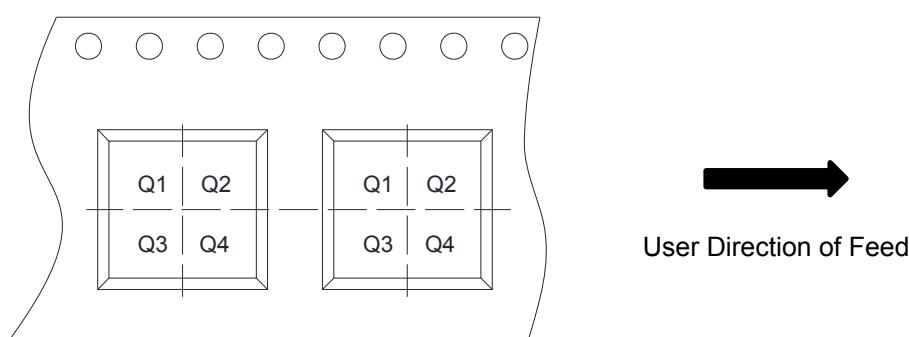

Capacitance

Body diode forward voltage

Single pulse power

Safe operating power

Gate charge Characteristics



Transient thermal response (Junction-to-Ambient)

Package outline dimensions
SOT-323

TOP VIEW

SIDE VIEW

SIDE VIEW

Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.80	0.95	1.10
A1	0.00	-	0.10
A2	0.65	0.83	1.00
b	0.20	0.30	0.40
c	0.05	-	0.15
D	1.90	2.05	2.20
E	1.15	1.25	1.35
E1	2.00	2.23	2.45
e	1.20	1.30	1.40
L	0.20	0.33	0.46
θ	0°	-	8°

TAPE AND REEL INFORMATION
Reel Dimensions

Tape Dimensions

Quadrant Assignments For PIN1 Orientation In Tape


RD	Reel Dimension	<input checked="" type="checkbox"/> 7inch	<input type="checkbox"/> 13inch		
W	Overall width of the carrier tape	<input checked="" type="checkbox"/> 8mm	<input type="checkbox"/> 12mm <input type="checkbox"/> 16mm		
P1	Pitch between successive cavity centers	<input type="checkbox"/> 2mm	<input checked="" type="checkbox"/> 4mm	<input type="checkbox"/> 8mm	
Pin1	Pin1 Quadrant	<input type="checkbox"/> Q1	<input type="checkbox"/> Q2	<input checked="" type="checkbox"/> Q3	<input type="checkbox"/> Q4